



ATP102

P-Channel Power MOSFET -30V, -40A, 18.5mΩ, Single ATPAK

ON Semiconductor®

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Features

- Low ON-resistance
- Slim package
- Halogen free compliance
- Large current
- 4.5V drive
- Protection diode in

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-40	A
Drain Current (PW≤10μs)	I _{DP}	PW≤10μs, duty cycle≤1%	-120	A
Allowable Power Dissipation	P _D	Tc=25°C	40	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		58	mJ
Avalanche Current *2	I _{AV}		20	A

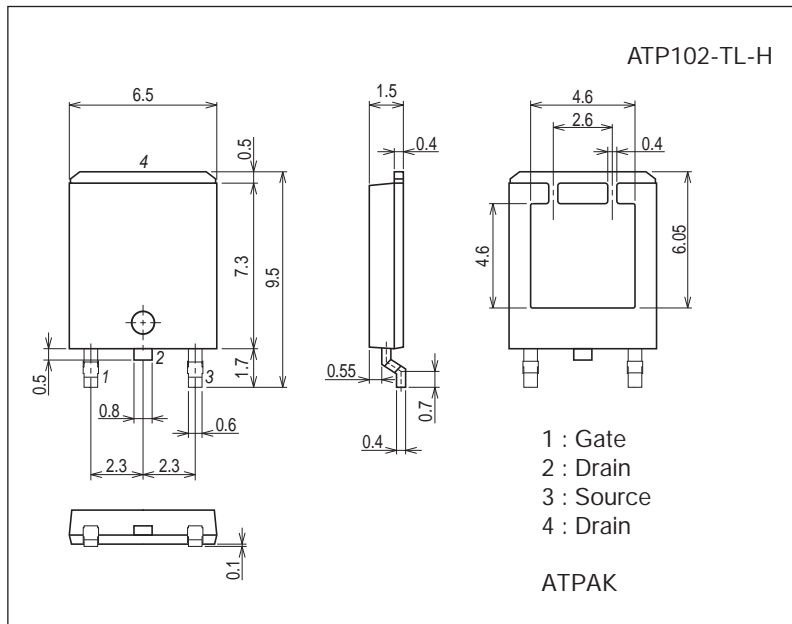
Note : *1 V_{DD}=10V, L=200μH, I_{AV}=20A
*2 L≤200μH, Single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

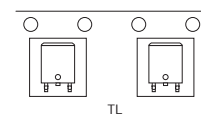
7057-001



Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

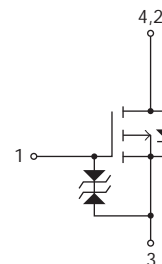
Packing Type: TL



Marking



Electrical Connection

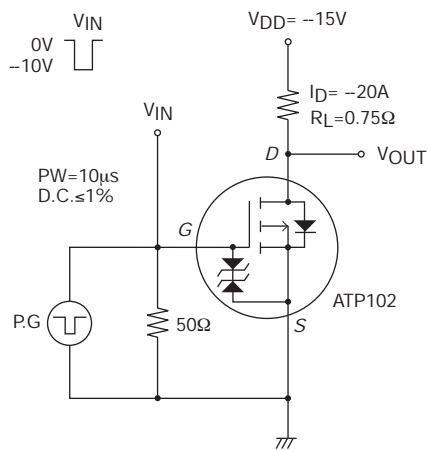


ATP102

Electrical Characteristics at Ta=25°C

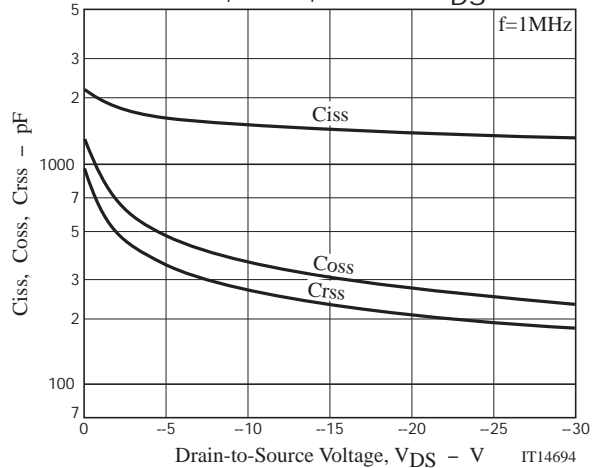
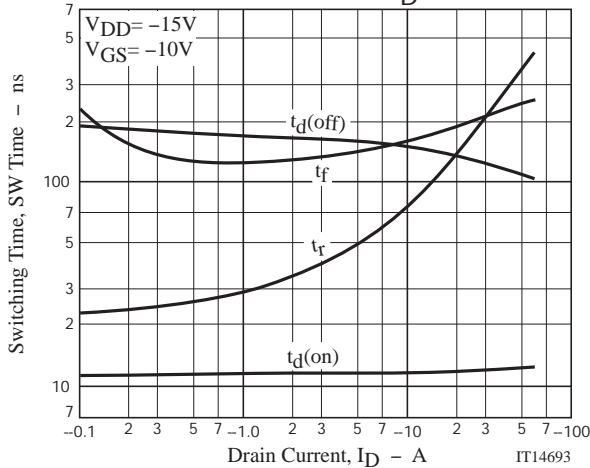
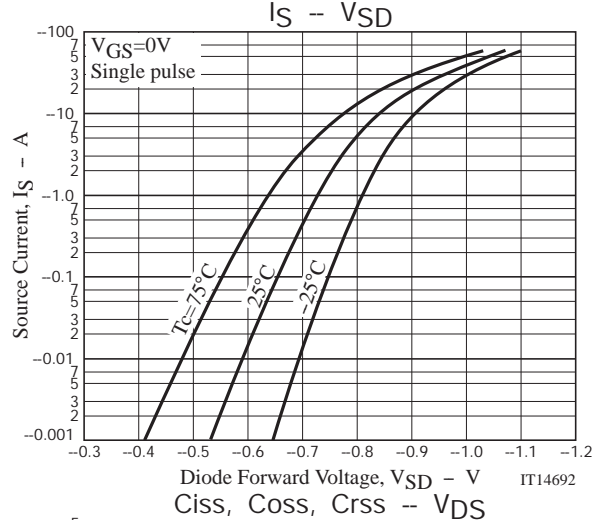
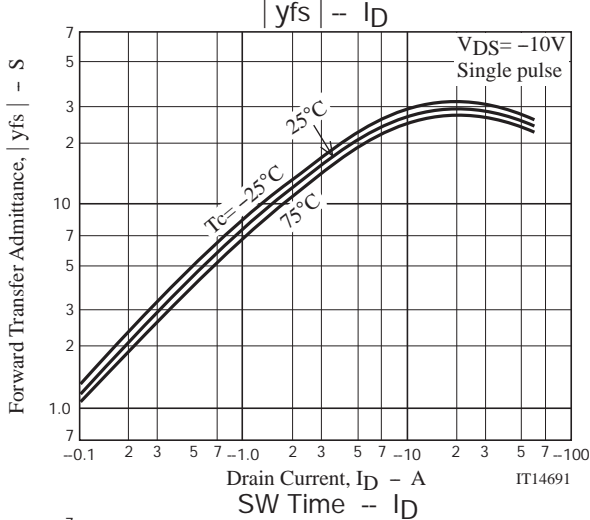
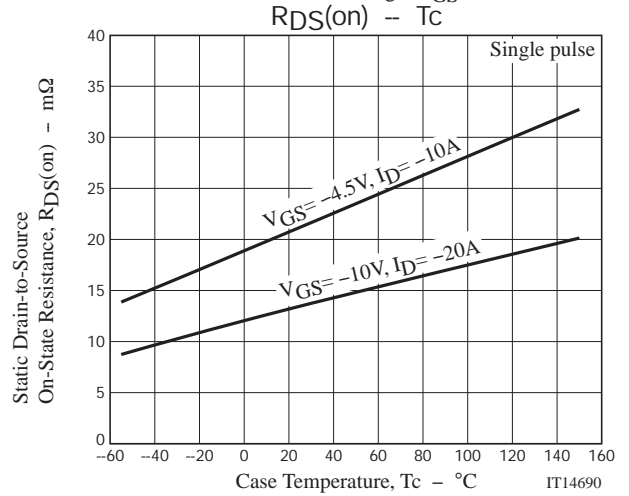
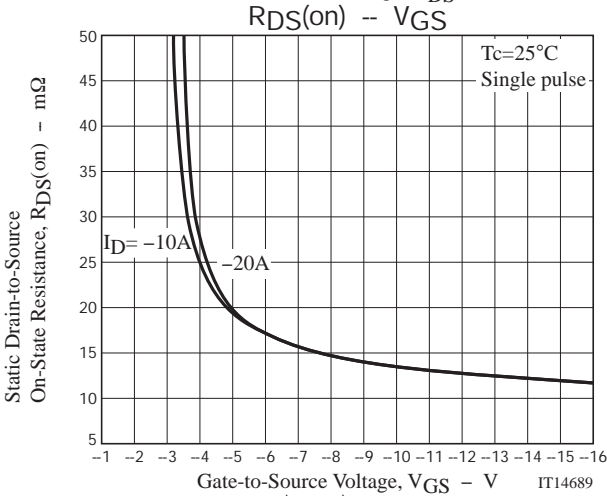
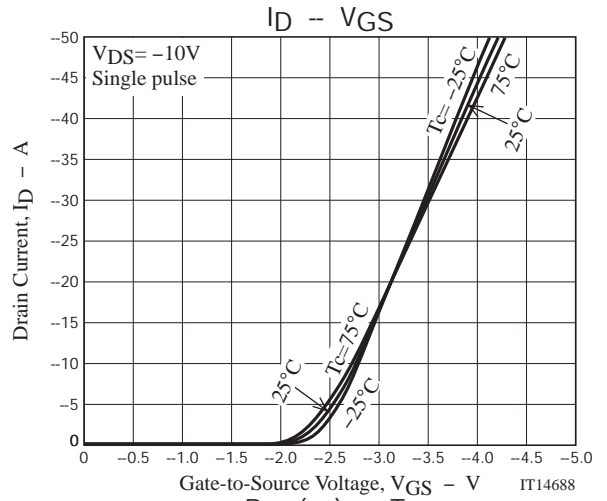
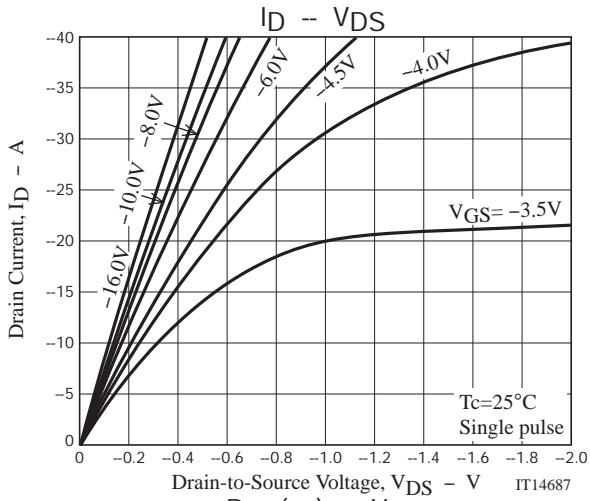
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-20A		29		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-20A, V _{GS} =-10V		14	18.5	mΩ
	R _{DS(on)2}	I _D =-10A, V _{GS} =-4.5V		22	31	mΩ
Input Capacitance	C _{iss}	V _{DS} =-10V, f=1MHz		1490		pF
Output Capacitance	C _{oss}			360		pF
Reverse Transfer Capacitance	C _{rss}			270		pF
Turn-ON Delay Time	t _{d(on)}			11		ns
Rise Time	t _r	See specified Test Circuit.		135		ns
Turn-OFF Delay Time	t _{d(off)}			135		ns
Fall Time	t _f			185		ns
Total Gate Charge	Q _g			34		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =-15V, V _{GS} =-10V, I _D =-40A		4.2		nC
Gate-to-Drain "Miller" Charge	Q _{gd}			11.5		nC
Diode Forward Voltage	V _{SD}		I _S =-40A, V _{GS} =0V	-0.99	-1.5	V

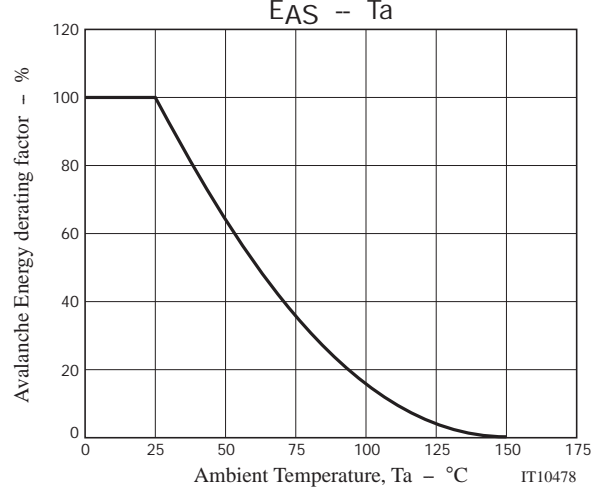
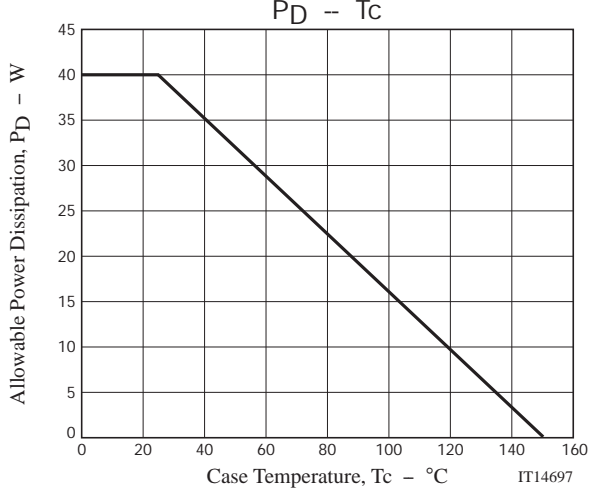
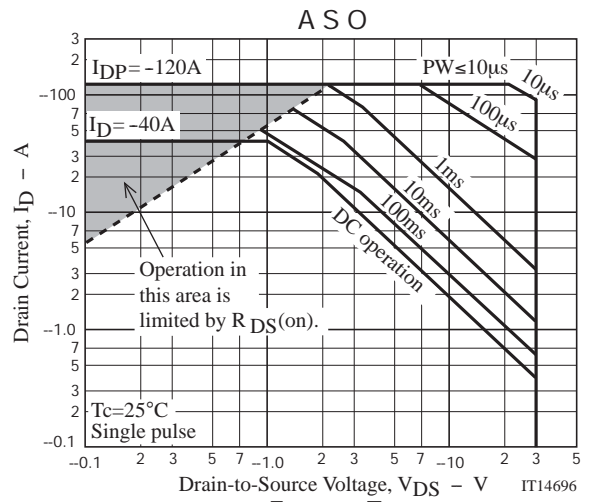
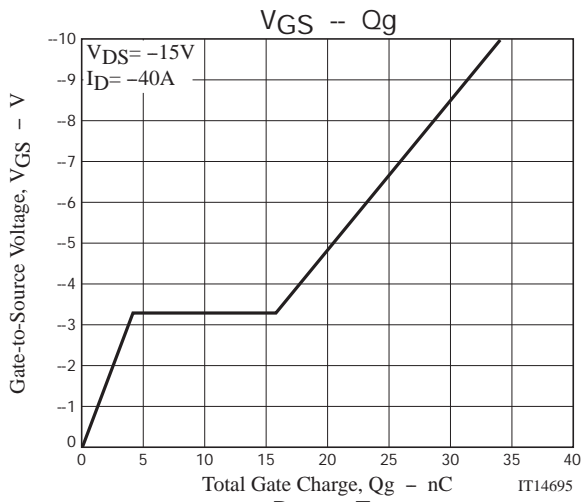
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ATP102-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free





Taping Specification

ATP102-TL-H

1. Packing Format (TL)

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
ATPAK	ATP	3,000	3,000	15,000	1 reels contained Dimensions:mm (external) 340×340×28	5 inner boxes contained Dimensions:mm (external) 355×355×165

Packing method



Reel label

Reel label, Inner box label
(unit:mm)



Outer box label

It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.



NOTE (1)

The LEAD FREE # description shows that the surface treatment of the terminal is lead free.

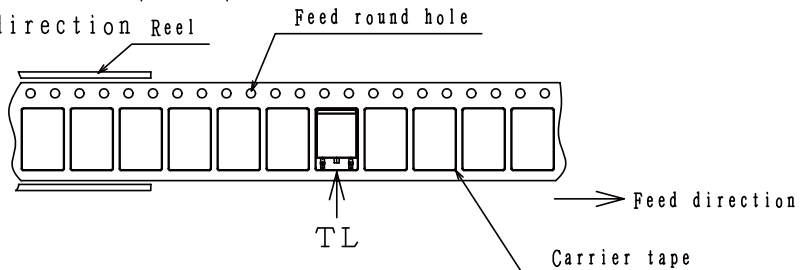
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction Reel



The one electrode terminals on feed hole side...TL

Note on usage : Since the ATP102 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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